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Part 2

# Highly Integrated Solution for AC Adapters: Experimental Results

A prototype of the highly-integrated boundary-conduction mode (BCM) PFC and quasi-resonant (QR) PWM combo controller exhibits efficiencies in the 90% range and harmonic distortion in the 3.75% to 14% range, depending on the ac input voltage and frequency.



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The experimental platform for the BCM/QR converter was a 19-V/90-W, universal input-voltage notebook adapter. Figs. 1 and 2 show the PFC switching waveform around the peak and valley of input voltage,  $V_g$ .

When the inductor current of the PFC choke discharges to zero, the inductor and parasitic capacitor of the PFC MOSFETs both resonate with each other. Then, the drain-to-source voltage,  $V_{DS}$ , of the PFC MOSFET starts to swing down, as does the voltage signal on the zero-current detection pin, F2.

Once the voltage is lower than the threshold voltage, the PFC gate will turn on. Around the peak of  $v_g$ , the switching cycle begins at the valley of  $V_{DS}$ . In this condition, the MOSFET turns on with zero current switching (ZCS). Around the valley of  $V_g$ , as shown in Fig. 2, each of the switching cycles begin after the inhibit time.

If  $V_{DS}$  has not swung back, then the MOSFET also turns on with zero voltage switching (ZVS). The power factor and THD test results shown in Table 1 are less than the limit of IEC1000-3-2 Class D with great margin.

The switching behavior of the PWM MOSFET from full load to no load is shown in Figs. 3 to 6. At full-load conditions,  $t_{OFF-MIN}$  is about 8 ms with the appropriate transformer design, and the PWM MOSFET will turn on at the first valley (Fig. 3). As the output loading is decreased,  $t_{OFF-MIN}$  is extended internally.

TABLE 1. PF AND THD TEST RESULTS

INPUT VOLTAGE		PF	THD (%)
90 V/60 Hz	$P_{in} = 75$ W	0.998	5.00
	Max. Load	0.999	3.75
115 V/60 Hz	$P_{in} = 75$ W	0.996	5.54
	Max. Load	0.998	4.21
240 V/50 Hz	$P_{in} = 75$ W	0.965	11.37
	Max. Load	0.978	8.76
264 V/50 Hz	$P_{in} = 75$ W	0.951	14.04
	Max. Load	0.969	10.25

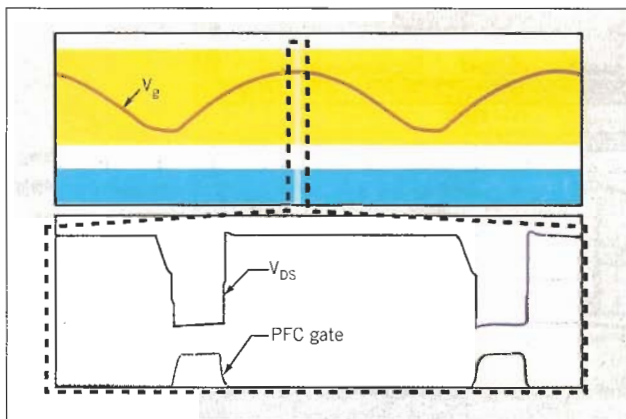


Fig. 1. BCM/QR controller performance with a 230-Vac full load, around the peak of input voltage,  $v_g$ .

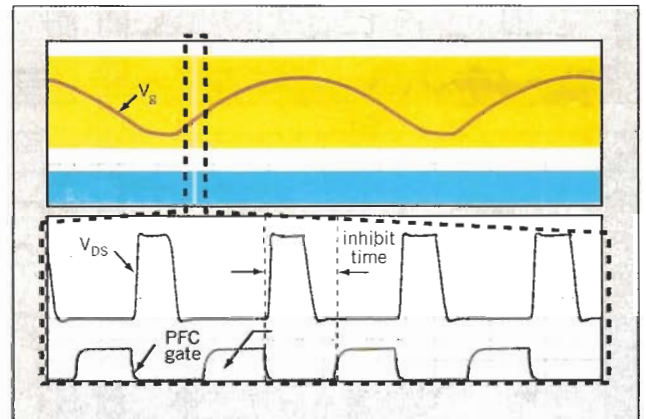


Fig. 2. BCM/QR controller performance with a 230-Vac full load, around the valley of input voltage,  $v_g$ .

During  $t_{OFF-MIN}$ , every valley signal is ignored. After  $t_{OFF-MIN}$  is passed, the PWM MOSFET turns on as the valley is detected. As is shown in Figs. 4 and 5, the valley of the PWM switch is extended as output loading is decreasing. Even the 14th valley can be detected at light-load condition.

Fig. 6 shows the PWM burst-mode operation at no-load condition. The switching frequency between each group of the PWM gate is about 60 Hz.

In each group, the switching frequency is decided by the level of  $V_{FB}$ , which is about 28 kHz, so the audible noise is extremely low. With extended-valley switching and burst-mode operation, the controller performs low-power consumption and low switching loss at no-load and light-load condition.

The test result is in Table 2. Table 3 shows the efficiency from 22.5% to 100% full load and from 90 to 264 Vac. Efficiency is in excess of 87% in each loading point.

This new combo solution (BCM PFC+QR PWM) has a simple and compact configuration. This converter can achieve high efficiency at high input voltages.

Besides very low switching loss, the power savings from this converter is lower than a traditional PFC+PWM converter because of the two-level PFC and deep extended valley detection. When looking at efficiency, the rectifier shows that this converter can achieve roughly a 1.5% to 2% improvement. Ⓞ

INPUT WATTAGE (W)	INPUT VOLTAGE (Vac)	INPUT WATTAGE (W)	OUTPUT WATTAGE (W)
0	115	0	0.162
	230	0	0.186
0.25	115	0.25	0.475
	230	0.25	0.493
0.5	115	0.509	0.779
	230	0.509	0.790
1	115	1.006	1.373
	230	1.006	1.380
1.15	115	1.152	1.539
	230	1.152	1.536
1.5	115	1.526	1.998
	230	1.526	2.003
1.7	115	1.7	2.196
	230	1.7	2.207

	22.5 W (25%)	45 W (50%)	67.5 W (75%)	90 W (100%)
90 Vac/ 60 Hz	88.92%	89.50%	89.39%	88.66%
115 Vac/ 60 Hz	90.60%	90.09%	90.29%	89.77%
230 Vac/ 50 Hz	90.20%	89.58%	90.60%	90.98%
264 Vac/ 50 Hz	90.19%	89.17%	90.64%	91.12%

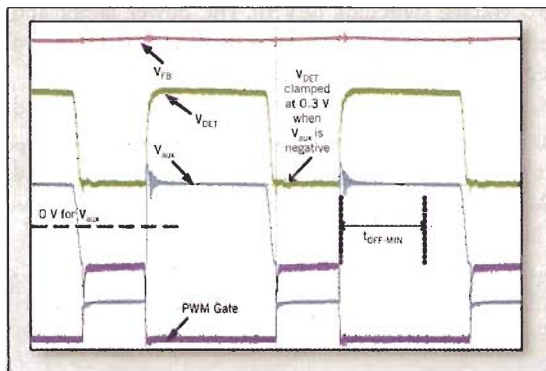


Fig. 3

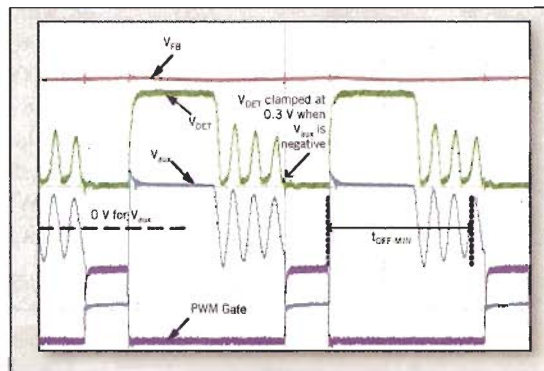


Fig. 4

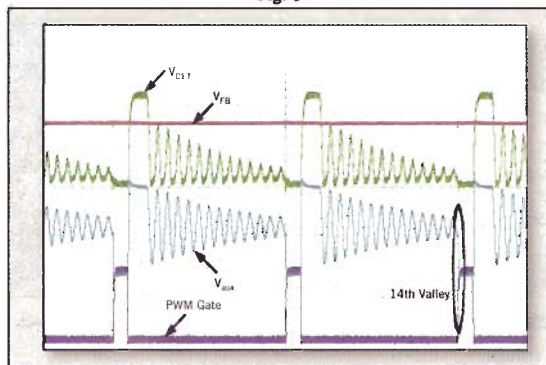


Fig. 5

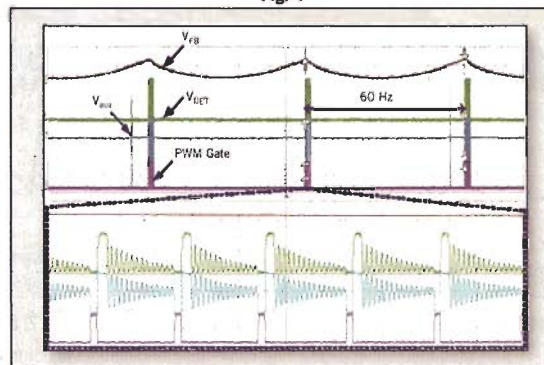


Fig. 6

Fig. 3. The switching behavior of the PWM MOSFET with a 115-Vac full load (left), while Fig. 4 (right) features a 115-Vac middle load.

Fig. 5. The switching behavior of the PWM MOSFET with a 115-Vac light load (left) and Fig. 6 (right) with a 115-Vac no load.